

ABSTRACT OF THE DISCLOSURE

A thin film transistor and a method of manufacturing the same includes forming a copper alloy line on substrate, an oxidation film formed on the upper surface of the copper alloy line. The copper alloy line includes a concentration y of magnesium, and the copper alloy line has a thickness t . the concentration y of magnesium in copper alloy line is related to the thickness is as follows:

$$y \leq \frac{94}{t}$$